

## Cascadable Silicon Bipolar MMIC Amplifier

# **Technical Data**

**MSA-0386** 

### **Features**

- Cascadable 50  $\Omega$  Gain Block
- **3 dB Bandwidth:** DC to 2.4 GHz
- 12.0 dB Typical Gain at 1.0 GHz
- 10.0 dBm Typical  $P_{1 dB}$  at 1.0 GHz
- Unconditionally Stable (k>1)
- Surface Mount Plastic Package
- Tape-and-Reel Packaging Option Available<sup>[1]</sup>

#### Note:

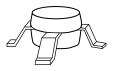
1. Refer to PACKAGING section "Tapeand-Reel Packaging for Surface Mount Semiconductors".

### **Description**

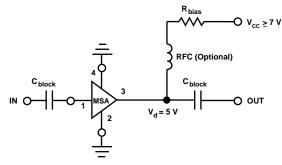
The MSA-0386 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a low cost, surface mount plastic package. This MMIC is designed for use as a general purpose 50  $\Omega$  gain block. Typical applications include narrow and broad band IF and RF amplifiers in commercial and industrial applications.

The MSA-series is fabricated using HP's 10 GHz  $f_T$ , 25 GHz  $f_{MAX}$ , silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

### 86 Plastic Package



### **Typical Biasing Configuration**



### MSA-0386 Absolute Maximum Ratings

Parameter	er Absolute Maximum <sup>[1]</sup>	
Device Current	70 mA	
Power Dissipation <sup>[2,3]</sup>	400 mW	
RF Input Power	+13dBm	
Junction Temperature	150°C	
Storage Temperature	−65 to 150°C	

Thermal Resistance<sup>[2,4]</sup>:  $\theta_{jc} = 115^{\circ}C/W$ 

### Notes:

- 1. Permanent damage may occur if any of these limits are exceeded.
- 2.  $T_{CASE} = 25$ °C.
- 3. Derate at 9.5 mW/°C for  $T_C > 116$ °C.

4. See MEASUREMENTS section "Thermal Resistance" for more information.

Symbol	Parameters and Test Conditions: $I_d$ = 35 mA, $Z_0$ = 50 $\Omega$		Units	Min.	Тур.	Max.
GP	Power Gain $( S_{21} ^2)$	f = 0.1  GHz f = 1.0  GHz	dB	10.0	12.5 12.0	
$\Delta G_P$	Gain Flatness	f = 0.1  to  1.6  GHz	dB		± 0.7	
f <sub>3 dB</sub>	3 dB Bandwidth		GHz		2.4	
VSWR	Input VSWR	f = 0.1 to $3.0$ GHz			1.5:1	
	Output VSWR	f = 0.1 to $3.0$ GHz			1.7:1	
NF	$50 \Omega$ Noise Figure	f = 1.0  GHz	dB		6.0	
$P_{1dB}$	Output Power at 1 dB Gain Compression	f = 1.0  GHz	dBm		10.0	
IP <sub>3</sub>	Third Order Intercept Point	f = 1.0  GHz	dBm		23.0	
$t_{\rm D}$	Group Delay	f = 1.0  GHz	psec		140	
Vd	Device Voltage		V	4.0	5.0	6.0
dV/dT	Device Voltage Temperature Coefficient		mV/°C		-8.0	

## Electrical Specifications<sup>[1]</sup>, $T_A = 25^{\circ}C$

#### Note:

1. The recommended operating current range for this device is 20 to 40 mA. Typical performance as a function of current is on the following page.

### **Part Number Ordering Information**

Part Number	No. of Devices	Container	
MSA-0386-TR1	1000	7" Reel	
MSA-0386-BLK	100	Antistatic Bag	

For more information, see "Tape and Reel Packaging for Semiconductor Devices".

 $\mathbf{S}_{22}$  $S_{21}$  $S_{11}$  $S_{12}$ Freq. GHz Mag Ang dB Mag dB Mag Ang Mag Ang Ang 4.22 12.5-18.3 .1220.1 .11 1741751 .13 -11 0.2 16912.54.20 170 -18.2.124  $\mathbf{2}$ .13 -20.11 159 12.4 159 -18.1.124 5-41 0.4 .11 4.16 .14 0.6 .10 149 12.2 4.09 149 -17.9.128 8 -60 .15 14212.1139 -17.6.131 9 -78 0.8 .10 4.00 .16 1.0 137 11.9 129 -17.4.136 11 -93 .09 3.93 .18 1.5.09 139 11.23.61106 -16.6.149 14 .20 -1292.0 .12 149 10.3 3.28 83 -15.3.171 13 .23 -1572.52.95 66 12 .26 -176.18 1509.4 -14.4.190 .29 3.0 .25 142 8.3 2.60 48 -13.7 .207 9 167 .32 3 3.5 133 7.22.2931 -13.2.219 .30 152.40 124 6.0 2.01 15 -13.0.224 -1 .31 142 4.0 .228 5.0.53 106 3.7 1.53-13-12.8-11.32 128

MSA-0386 Typical Scattering Parameters ( $Z_0 = 50 \Omega$ ,  $T_A = 25^{\circ}C$ ,  $I_d = 35 mA$ )

A model for this device is available in the DEVICE MODELS section.

### Typical Performance, $T_A = 25^{\circ}C$

(unless otherwise noted)

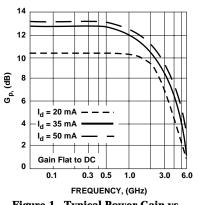


Figure 1. Typical Power Gain vs. Frequency,  $T_A = 25^{\circ}C$ .

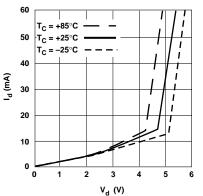


Figure 2. Device Current vs. Voltage.

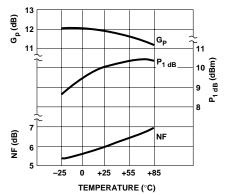


Figure 3. Output Power at 1 dB Gain Compression, NF and Power Gain vs. Case Temperature, f = 1.0 GHz,  $I_d=35$ mA.

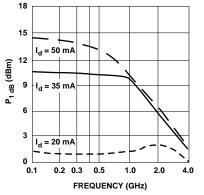


Figure 4. Output Power at 1 dB Gain Compression vs. Frequency.

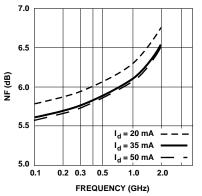
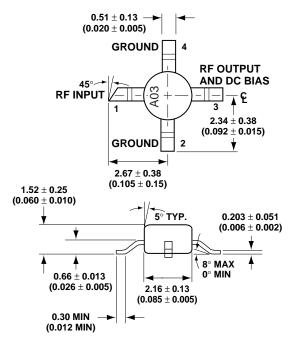


Figure 5. Noise Figure vs. Frequency.

### **86 Plastic Package Dimensions**



DIMENSIONS ARE IN MILLIMETERS (INCHES)